

**Amendments to the Claims**

This listing of claims will replace all prior versions, and listings, of claims in the application.

**Listing of Claims:**

1. (Original) A thin film magnetic memory device comprising:
  - a plurality of memory regions, arranged in a column direction, each having a plurality of memory cells arranged in a matrix, wherein
    - each of said memory regions includes:
      - a plurality of bit lines provided in correspondence with memory cell columns, respectively;
      - a first driver band arranged in a first direction of said plurality of bit lines, and supplied with power for supplying a data write current to at least one bit line among said plurality of bit lines; and
      - a second driver band arranged in a second direction opposite to said first direction of said plurality of bit lines, and supplied with the power for supplying said data write current to at least one bit line among said plurality of bit lines,
  - said thin film magnetic memory device further comprises:
    - a first pair of power supply line, arranged in the column direction, for supplying the power to said first driver band from said first direction; and
    - a second pair of power supply line, arranged in the column direction, for supplying the power to said second driver band from said second direction,
  - each of said first and second pair of power supply lines includes first and second power lines supplying a first voltage and a second voltage, respectively, and

when data is written, the first driver band corresponding to the selected memory region selected by an externally applied address designation among said plurality of memory regions is connected to one of the first and second power lines of said first pair of power supply line in accordance with written data, and the second driver band corresponding to said selected memory region is connected to the other one of said first and second power lines of said second pair of power supply line in accordance with said written data.

2. (Original) The thin film magnetic memory device according to claim 1, wherein said first power supply line is arranged to extend over said plurality of memory regions, and

no current path is formed in a region of each of said first and second pair of power supply lines, which corresponds to said selected memory region selected from said plurality of memory regions.

3. (Original) The thin film magnetic memory device according to claim 1, wherein said data write current carried to at least one of said plurality of bit lines is equal in direction to said data write current carried to said first and second pair of power supply lines.

4. (Original) The thin film magnetic memory device according to claim 1, further comprising:

first and second power supply terminals supplied with said first voltage; and

third and fourth power supply terminals supplied with said second voltage, wherein

said first and third power supply terminals are arranged in said first direction of said first pair of power supply line, and are connected to the first and second power lines of said first pair of power supply line, respectively, and

said second and fourth power supply terminals are arranged in said second direction of said second pair of power supply line, and are connected to the first and second power lines of said second pair of power supply line, respectively.

5. (Previously Presented) The thin film magnetic memory device according to claim 1, wherein

said data write current carried to the at least one bit line by said first or second driver flows in at least one of said first direction and said second direction.

6. (Original) The thin film magnetic memory device according to claim 1, wherein each of said memory regions is divided into a plurality of block regions in a row direction,

said first driver band is divided into a plurality of first driver units corresponding to said plurality of block regions in the row direction, respectively,

said second driver band is divided into a plurality of second driver units corresponding to said plurality of block regions in the row direction, respectively,

said first and second pair of power supply lines are further provided for every group block regions constituting the same column in said plurality of memory regions,

said written data includes data of a plurality of bits corresponding to said plurality of block regions, respectively, and

in each of said block regions belonging to said selected memory region, the corresponding first driver unit is connected to one of the first and second power lines of said first pair of power supply line in accordance with the data of a corresponding bit among said plurality of bits, and the corresponding second driver unit is connected to the other one of said first and second power lines of said second pair of power supply line in accordance with the data of said corresponding bit among said plurality of bits.

7. (Original) The thin film magnetic memory device according to claim 6, wherein each said first pair of power supply line further includes a first sub-power supply line arranged in a direction in which the first sub-power supply line intersects with said first and second power lines, and provided for each of the first driver units corresponding to each of said block regions,

each said second pair of power supply line further includes a second sub-power supply line arranged in a direction in which the second sub-power supply line intersects with said first and second power lines, and provided for each of the second driver units corresponding to each of said block regions,

in each of said block regions belonging to said selected region, said corresponding first driver unit is connected to one of said first and second power lines through said first sub-power supply line corresponding to said each first driver unit, and

said corresponding second driver unit is connected to the other one of said first and second power lines through said second sub-power supply line corresponding to said each second driver unit.

8. (Original) A thin film magnetic memory device comprising:

a plurality of memory regions, arranged in a column direction, each having a plurality of memory cells arranged in a matrix, wherein

each of said memory regions includes:

a plurality of bit lines provided in correspondence with memory cell columns, respectively;

a first driver band arranged in a first direction of said plurality of bit lines, and supplied with power for supplying a data write current to at least one bit line among said plurality of bit lines; and

a second driver band arranged in a second direction opposite to said first direction of said plurality of bit lines, and supplied with the power for supplying said data write current to at least one bit line among said plurality of bit lines,

said thin film magnetic memory device further comprises:

a first power supply line, arranged in correspondence with said first driver band along the column direction, for supplying a first voltage from said first direction; and

a second power supply line, arranged in correspondence with said second driver band along the column direction, for supplying a second voltage from said second direction,

when data is written, one of the first and second driver bands corresponding to the selected memory region selected from said plurality of memory regions in accordance with

written data is connected to one of the corresponding first and second power supply lines, and the other one of said corresponding first and second driver bands is electrically connected to the second voltage.

9. (Previously Presented) A thin film magnetic memory device comprising:

a plurality of memory regions, arranged in a row direction, each having a plurality of memory cells arranged in a matrix, wherein

each of said memory regions includes:

a plurality of digit lines provided in correspondence with memory cell rows, respectively;

and

a digit line driver band arranged in a first direction of said plurality of digit lines, and supplied with a first voltage for supplying a data write current to at least one digit line selected from said plurality of digit lines,

each of said digit lines is supplied with a second voltage from a second direction opposite to said first direction, and

said thin film magnetic memory device further comprises a first power supply line, electrically coupled to said digit line driver band in the row direction, for supplying said first voltage from said first direction.

10. (Original) The thin film magnetic memory device according to claim 9, further comprising:

a second power supply line supplying said second voltage from said second direction,

wherein

in each of said memory regions, said plurality of digit lines in said second direction are electrically coupled to said second power supply line.

11. (New) A thin film magnetic memory device comprising:
- a plurality of memory regions, arranged in a column direction, each having a plurality of memory cells arranged in a matrix, wherein
- each of said memory regions includes:
- a plurality of bit lines provided in correspondence with memory cell columns, respectively;
- said thin film magnetic memory device further comprising:
- power supply lines for supplying power to a current driver for supplying a data write current to said bit lines, wherein
- said power supply lines are arranged to extend over said plurality of memory regions, and
- no current path is formed in a region of each of said power supply lines that corresponds to a selected memory region selected for a data write operation from said plurality of memory regions.